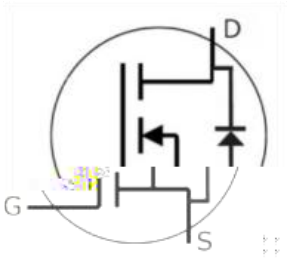
SG2M020170BK(Preliminary)

TriQSiC™ 1700V Silicon Carbide Power MOSFET G2

Features

-
-
-
-
-



Benefits

-
-
-
-
-

Part number	Die size W x L mm

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS} ≤	$R_{DS(on),\ typ}$	$T_{J,max}$

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1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note

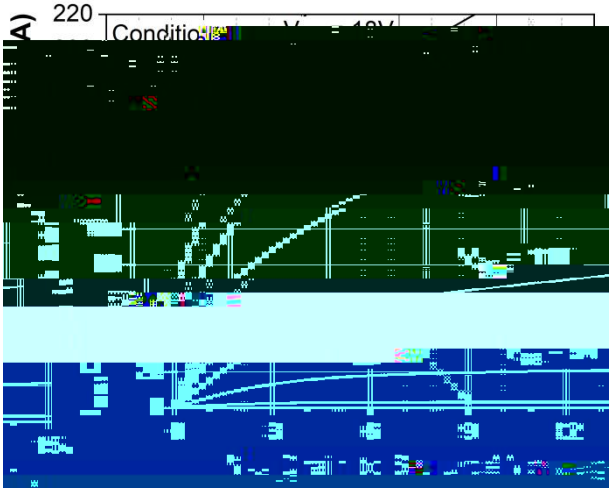
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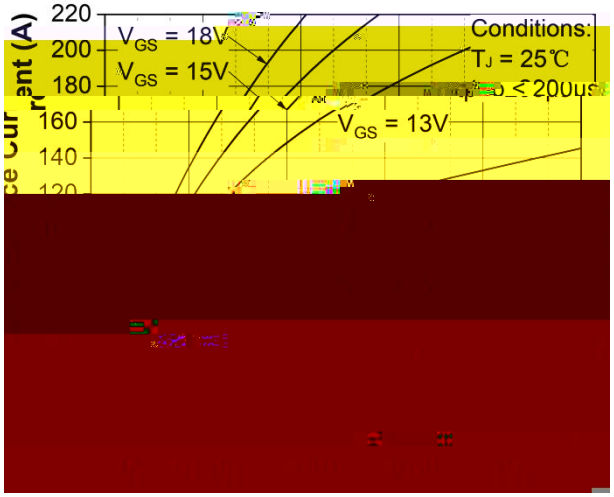
2.3 Switching characteristics

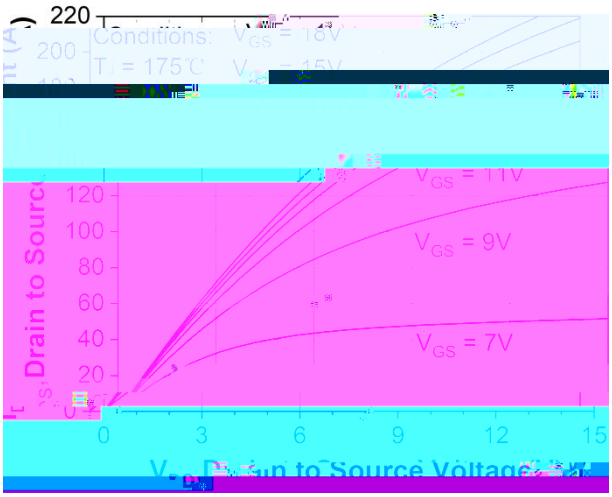
Table 5 Dynamic characteristics

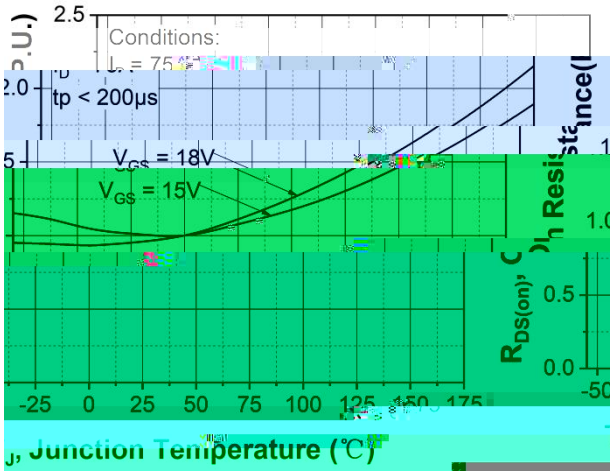
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

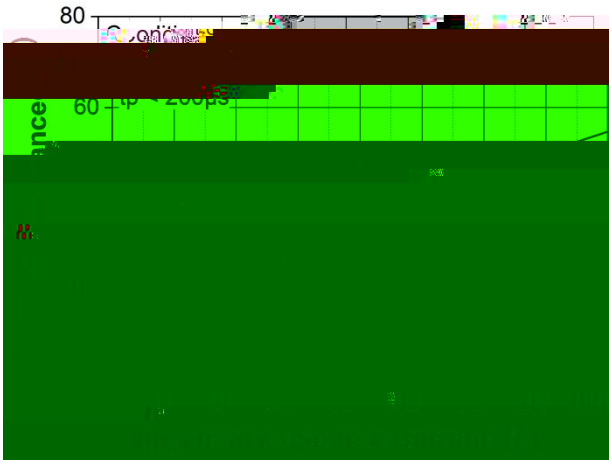
3 Electrical characteristic diagrams







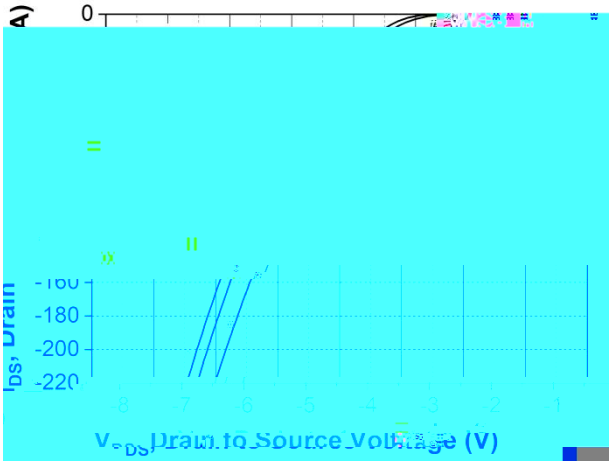


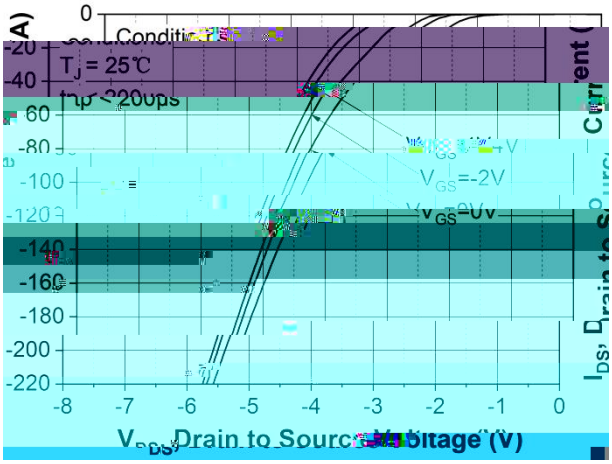


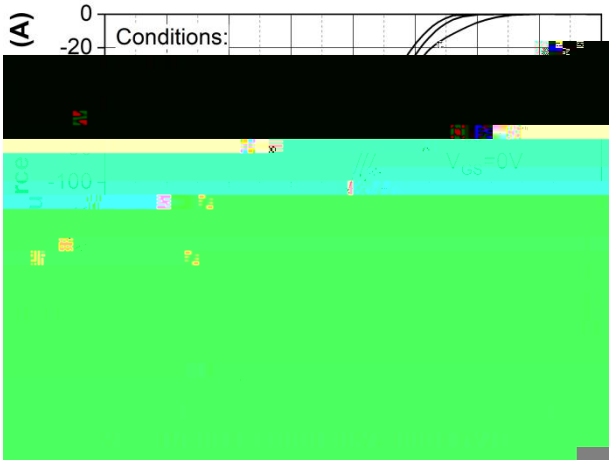


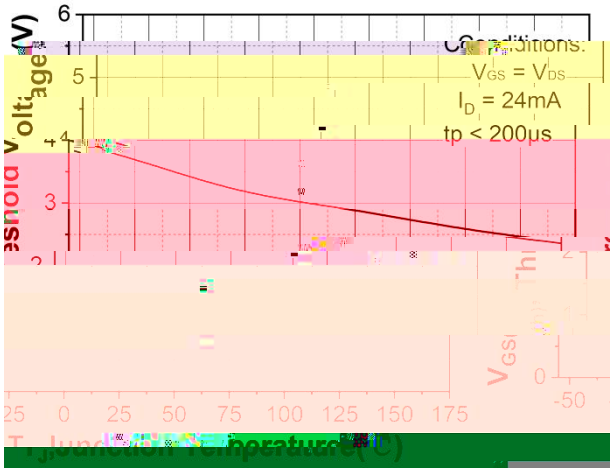
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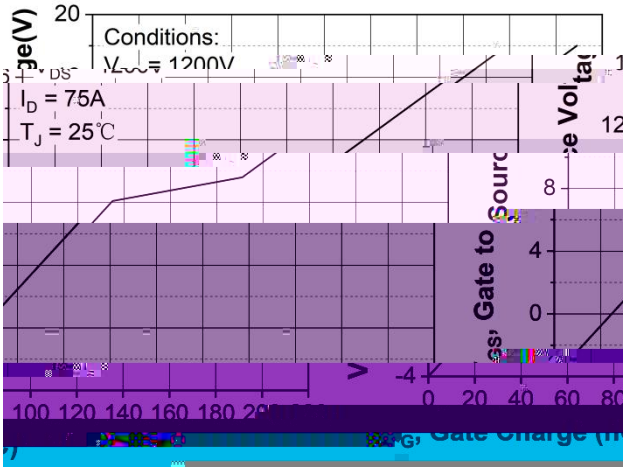




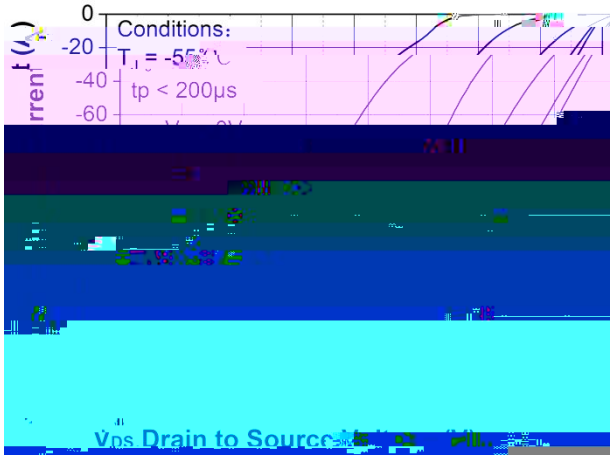








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4 Mechanical parameters

4.1 Dimensions and metallization

Parameter	Typical value	Unit	Metallization

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SG2M020170BK

1700V SiC Power MOSFET

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2025-12-04	——	——
V01_01	2025-12-30	Preliminary	——

Attention

Rohs compliance

SG2M020170BK